

ADG711/ADG712/ADG713

FEATURES

1.8 V to 5.5 V single supply
Low on resistance (2.5 Ω Typ)
Low on resistance flatness
-3 dB bandwidth > 200 MHz
Rail-to-rail operation
16-lead TSSOP and SOIC packages
Fast switching times: $t_{ON} = 16$ ns, $t_{OFF} = 10$ ns
Typical power consumption (< 0.01 μ W)
TTL/CMOS compatible
Qualified for automotive applications

APPLICATIONS

USB 1.1 signal switching circuits
Cell phones
PDA's
Battery-powered systems
Communication systems
Sample hold systems
Audio signal routing
Video switching
Mechanical reed relay replacement

GENERAL DESCRIPTION

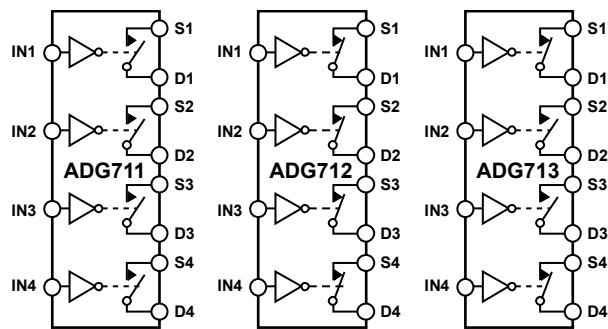
The **ADG711**, **ADG712**, and **ADG713** are monolithic CMOS devices containing four independently selectable switches. These switches are designed on an advanced submicron process that provides low power dissipation yet gives high switching speed, low on resistance, low leakage currents, and high bandwidth.

They are designed to operate from a single 1.8 V to 5.5 V supply, making them ideal for use in battery-powered instruments and with the new generation of DACs and ADCs from Analog Devices, Inc. Fast switching times and high bandwidth make the parts suitable for switching USB 1.1 data signals and video signals.

The **ADG711**, **ADG712**, and **ADG713** contain four independent single-pole/single-throw (SPST) switches. The **ADG711** and **ADG712** differ only in that the digital control logic is inverted. The **ADG711** switches are turned on with a logic low on the appropriate control input, while a logic high is required to turn on the switches of the **ADG712**. The **ADG713** contains two switches whose digital control logic is similar to the **ADG711**, while the logic is inverted on the other two switches.

Each switch conducts equally well in both directions when On. The **ADG713** exhibits break-before-make switching action.

FUNCTIONAL BLOCK DIAGRAM



SWITCHES SHOWN FOR A LOGIC "1" INPUT

Figure 1.

0002-29000

The **ADG711/ADG712/ADG713** are available in 16-lead TSSOP and 16-lead SOIC packages.

PRODUCT HIGHLIGHTS

- 1.8 V to 5.5 V Single-Supply Operation.
The **ADG711**, **ADG712**, and **ADG713** offer high performance and are fully specified and guaranteed with 3 V and 5 V supply rails.
- Very Low R_{ON} (4.5 Ω maximum at 5 V, 8 Ω maximum at 3 V).
At supply voltage of 1.8 V, R_{ON} is typically 35 Ω over the temperature range.
- Low On Resistance Flatness.
- 3 dB Bandwidth >200 MHz.
- Low Power Dissipation. CMOS construction ensures low power dissipation.
- Fast t_{ON}/t_{OFF} .
- Break-Before-Make Switching.
This prevents channel shorting when the switches are configured as a multiplexer (**ADG713** only).
- 16-Lead TSSOP and 16-Lead SOIC Packages.

Rev. B

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REVISION HISTORY

6/11—Rev. A to Rev. B

Updated Format.....	Universal
Changes to Features Section.....	1
Changes to Absolute Maximum Ratings Table.....	5
Changes to Ordering Guide	14
Added Automotive Products Section	14

3/04—Rev. 0 to Rev. A

Added Applications.....	1
Changes to Ordering Guide	4
Updated Outline Dimensions	10

SPECIFICATIONS

$V_{DD} = +5\text{ V} \pm 10\%$, $GND = 0\text{ V}$. All specifications -40°C to $+85^{\circ}\text{C}$, unless otherwise noted.

Table 1.

Parameter	+25°C	−40°C to +85°C	Unit	Test Conditions/Comments
ANALOG SWITCH				
Analog Signal Range		0 V to V_{DD}	V	
On Resistance (R_{ON})	2.5		Ω typ	$V_S = 0\text{ V}$ to V_{DD} , $I_S = -10\text{ mA}$;
	4	4.5	Ω max	See Figure 11
On Resistance Match Between Channels (ΔR_{ON})		0.05	Ω typ	$V_S = 0\text{ V}$ to V_{DD} , $I_S = -10\text{ mA}$
		0.3	Ω max	
On Resistance Flatness ($R_{FLAT(ON)}$)	0.5		Ω typ	$V_S = 0\text{ V}$ to V_{DD} , $I_S = -10\text{ mA}$
		1.0	Ω max	
LEAKAGE CURRENTS				
Source Off Leakage I_S (Off)	± 0.01		nA typ	$V_{DD} = +5.5\text{ V}$
	± 0.1	± 0.2	nA max	$V_S = 4.5\text{ V}/1\text{ V}$, $V_D = 1\text{ V}/4.5\text{ V}$
Drain Off Leakage I_D (Off)	± 0.01		nA typ	See Figure 12
	± 0.1	± 0.2	nA max	$V_S = 4.5\text{ V}/1\text{ V}$, $V_D = 1\text{ V}/4.5\text{ V}$
Channel On Leakage I_D , I_S (On)	± 0.01		nA typ	See Figure 12
	± 0.1	± 0.2	nA max	$V_S = V_D = 1\text{ V}$, or 4.5 V
				See Figure 13
DIGITAL INPUTS				
Input High Voltage, V_{INH}		2.4	V min	
Input Low Voltage, V_{INL}		0.8	V max	
Input Current I_{INL} or I_{INH}	0.005		μA typ	$V_{IN} = V_{INL}$ or V_{INH}
		± 0.1	μA max	
DYNAMIC CHARACTERISTICS¹				
t_{ON}	11		ns typ	$R_L = 300\ \Omega$, $C_L = 35\text{ pF}$
		16	ns max	$V_S = 3\text{ V}$; see Figure 14
t_{OFF}	6		ns typ	$R_L = 300\ \Omega$, $C_L = 35\text{ pF}$
		10	ns max	$V_S = 3\text{ V}$; see Figure 14
Break-Before-Make Time Delay, t_D (ADG713 Only)	6		ns typ	$R_L = 300\ \Omega$, $C_L = 35\text{ pF}$
		1	ns min	$V_{S1} = V_{S2} = 3\text{ V}$; see Figure 15
Charge Injection	3		pC typ	$V_S = 2\text{ V}$; $R_S = 0\ \Omega$, $C_L = 1\text{ nF}$; see Figure 16
Off Isolation	−58		dB typ	$R_L = 50\ \Omega$, $C_L = 5\text{ pF}$, $f = 10\text{ MHz}$
	−78		dB typ	$R_L = 50\ \Omega$, $C_L = 5\text{ pF}$, $f = 1\text{ MHz}$; see Figure 17
Channel-to-Channel Crosstalk	−90		dB typ	$R_L = 50\ \Omega$, $C_L = 5\text{ pF}$, $f = 10\text{ MHz}$; see Figure 18
Bandwidth −3 dB	200		MHz typ	$R_L = 50\ \Omega$, $C_L = 5\text{ pF}$; see Figure 19
C_S	10		pF typ	
C_D	10		pF typ	
C_D , C_S (On)	22		pF typ	
POWER REQUIREMENTS				
I_{DD}	0.001		μA typ	$V_{DD} = +5.5\text{ V}$
		1.0	μA max	Digital inputs = 0 V or 5 V

¹ Guaranteed by design, not subject to production test.

ADG711/ADG712/ADG713

$V_{DD} = +3\text{ V} \pm 10\%$, $GND = 0\text{ V}$. All specifications -40°C to $+85^{\circ}\text{C}$, unless otherwise noted.

Table 2.

Parameter	+25°C	−40°C to +85°C	Unit	Test Conditions/Comments
ANALOG SWITCH				
Analogue Signal Range		0 V to V_{DD}	V	
On Resistance (R_{ON})	5	5.5	Ω typ	$V_S = 0\text{ V}$ to V_{DD} , $I_S = -10\text{ mA}$; See Figure 11
		8	Ω max	
On Resistance Match Between Channels (ΔR_{ON})	0.1	0.3	Ω typ	$V_S = 0\text{ V}$ to V_{DD} , $I_S = -10\text{ mA}$
			Ω max	
On Resistance Flatness ($R_{FLAT(ON)}$)		2.5	Ω typ	$V_S = 0\text{ V}$ to V_{DD} , $I_S = -10\text{ mA}$
LEAKAGE CURRENTS				
Source Off Leakage I_S (Off)	± 0.01		nA typ	$V_{DD} = +3.3\text{ V}$ $V_S = 3\text{ V}/1\text{ V}$, $V_D = 1\text{ V}/3\text{ V}$
	± 0.1	± 0.2	nA max	See Figure 12
Drain Off Leakage I_D (Off)	± 0.01		nA typ	$V_S = 3\text{ V}/1\text{ V}$, $V_D = 1\text{ V}/3\text{ V}$
	± 0.1	± 0.2	nA max	See Figure 12
Channel On Leakage I_D , I_S (On)	± 0.01		nA typ	$V_S = V_D = 1\text{ V}$, or 3 V
	± 0.1	± 0.2	nA max	See Figure 13
DIGITAL INPUTS				
Input High Voltage, V_{INH}		2.0	V min	
Input Low Voltage, V_{INL}		0.4	V max	
Input Current I_{INL} or I_{INH}	0.005		μA typ	$V_{IN} = V_{INL}$ or V_{INH}
		± 0.1	μA max	
DYNAMIC CHARACTERISTICS¹				
t_{ON}	13		ns typ	$R_L = 300\ \Omega$, $C_L = 35\text{ pF}$
		20	ns max	$V_S = 2\text{ V}$; see Figure 14
t_{OFF}	7		ns typ	$R_L = 300\ \Omega$, $C_L = 35\text{ pF}$
		12	ns max	$V_S = 2\text{ V}$; see Figure 14
Break-Before-Make Time Delay, t_D (ADG713 Only)	7		ns typ	$R_L = 300\ \Omega$, $C_L = 35\text{ pF}$
		1	ns min	$V_{S1} = V_{S2} = 2\text{ V}$; see Figure 15
Charge Injection	3		pC typ	$V_S = 1.5\text{ V}$; $R_S = 0\ \Omega$, $C_L = 1\text{ nF}$; see Figure 16
Off Isolation	−58		dB typ	$R_L = 50\ \Omega$, $C_L = 5\text{ pF}$, $f = 10\text{ MHz}$
	−78		dB typ	$R_L = 50\ \Omega$, $C_L = 5\text{ pF}$, $f = 1\text{ MHz}$; see Figure 17
Channel-to-Channel Crosstalk	−90		dB typ	$R_L = 50\ \Omega$, $C_L = 5\text{ pF}$, $f = 10\text{ MHz}$; see Figure 18
Bandwidth −3 dB	200		MHz typ	$R_L = 50\ \Omega$, $C_L = 5\text{ pF}$; see Figure 19
C_S	10		pF typ	
C_D	10		pF typ	
C_D , C_S (On)	22		pF typ	
POWER REQUIREMENTS				
I_{DD}	0.001		μA typ	$V_{DD} = +3.3\text{ V}$ Digital inputs = 0 V or 3 V
		1.0	μA max	

¹ Guaranteed by design, not subject to production test.

ABSOLUTE MAXIMUM RATINGS

$T_A = +25^{\circ}\text{C}$, unless otherwise noted.

Table 3.

Parameter	Rating
V_{DD} to GND	$-0.3\text{ V to }+6\text{ V}$
Analog, Digital Inputs ¹	$-0.3\text{ V to }V_{DD}+0.3\text{ V}$ or 30 mA, whichever occurs first
Continuous Current, S or D	30 mA
Peak Current, S or D	100 mA (Pulsed at 1 ms, 10% duty cycle maximum)
Operating Temperature Range	$-40^{\circ}\text{C to }+85^{\circ}\text{C}$
Storage Temperature Range	$-65^{\circ}\text{C to }+150^{\circ}\text{C}$
Junction Temperature	150°C
TSSOP Package, Power Dissipation	430 mW
θ_{JA} Thermal Impedance	150°C/W
θ_{JC} Thermal Impedance	27°C/W
SOIC Package, Power Dissipation	520 mW
θ_{JA} Thermal Impedance	125°C/W
θ_{JC} Thermal Impedance	42°C/W
Lead Temperature, Soldering	
Vapor Phase (60 sec)	215°C
Infrared (15 sec)	220°C
Soldering(Pb-Free)	
Reflow, Peak Temperature	$260(+0/-5)^{\circ}\text{C}$
Time at Peak Temperature	20 sec to 40 sec
ESD	2 kV

¹ Overvoltages at IN, S or D will be clamped by internal diodes. Currents should be limited to the maximum ratings given.

Stresses above those listed under Absolute Maximum Ratings may cause permanent damage to the device. This is a stress rating only; functional operation of the device at these or any other conditions above those indicated in the operational section of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

Only one absolute maximum rating may be applied at any one time.

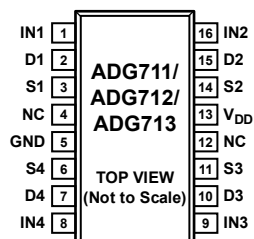
ESD CAUTION



ESD (electrostatic discharge) sensitive device. Charged devices and circuit boards can discharge without detection. Although this product features patented or proprietary protection circuitry, damage may occur on devices subjected to high energy ESD. Therefore, proper ESD precautions should be taken to avoid performance degradation or loss of functionality.

ADG711/ADG712/ADG713

PIN CONFIGURATION AND FUNCTION DESCRIPTIONS



NOTES
1. NC = NO CONNECT. DO NOT CONNECT TO THIS PIN.

00042-004

Figure 2. Pin Configuration

Table 4.

Pin Number	Mnemonic	Description
1	IN1	Digital Control Input. Its logic state controls the status of the Switch S1-D1.
2	D1	Drain Pin. Can be used as input or output.
3	S1	Source Pin. Can be used as input or output.
4	NC	Not internally connected.
5	GND	The most negative power supply pin.
6	S4	Source Pin. Can be used as input or output.
7	D4	Drain Pin. Can be used as input or output.
8	IN4	Digital Control Input. Its logic state controls the status of the Switch S4-D4.
9	IN3	Digital Control Input. Its logic state controls the status of the Switch S3-D3.
10	D3	Drain Pin. Can be used as input or output.
11	S3	Source Pin. Can be used as input or output.
12	NC	Not internally connected.
13	V _{DD}	The most positive power supply pin.
14	S2	Source Pin. Can be used as input or output.
15	D2	Drain Pin. Can be used as input or output.
16	IN2	Digital Control Input. Its logic state controls the status of the Switch S3-D3.

Table 5. Truth Table (ADG711/ADG712)

ADG711 In	ADG712 In	Switch Condition
0	1	On
1	0	Off

Table 6. Truth Table (ADG713)

Logic	Switch 1, 4	Switch 2, 3
0	Off	On
1	On	Off

TYPICAL PERFORMANCE CHARACTERISTICS

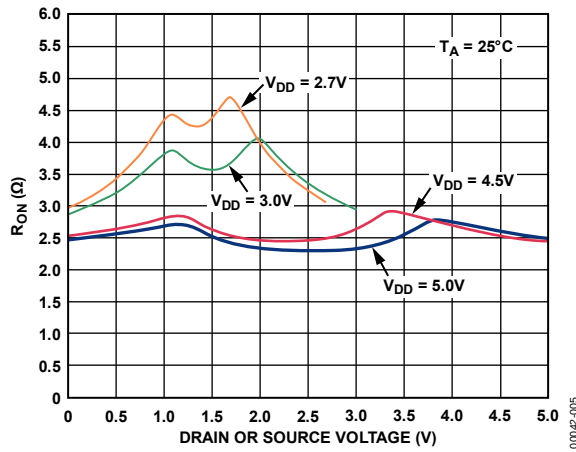


Figure 3. On Resistance as a Function of V_D (V_S)

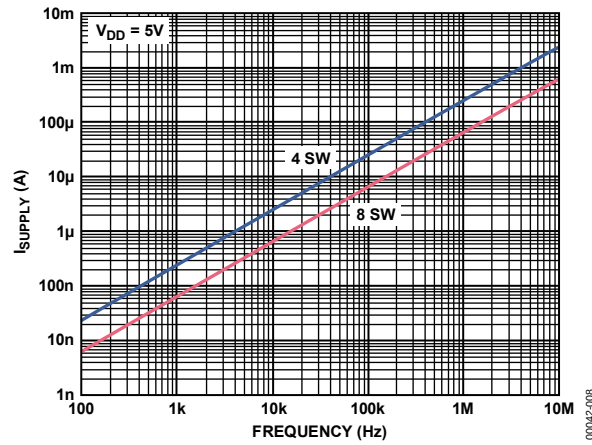


Figure 6. Supply Current vs. Input Switching Frequency

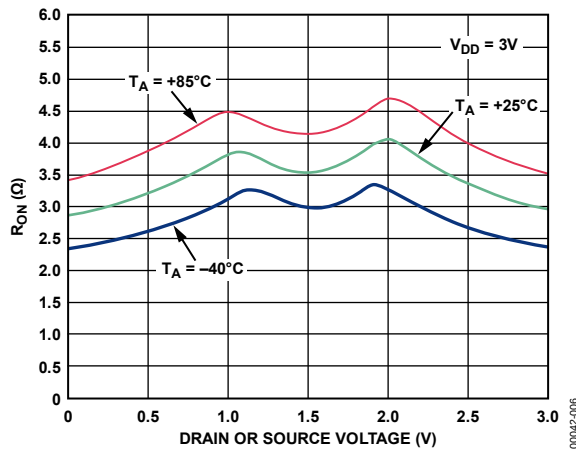


Figure 4. On Resistance as a Function of V_D (V_S) for Different Temperatures
 $V_{DD} = 3V$

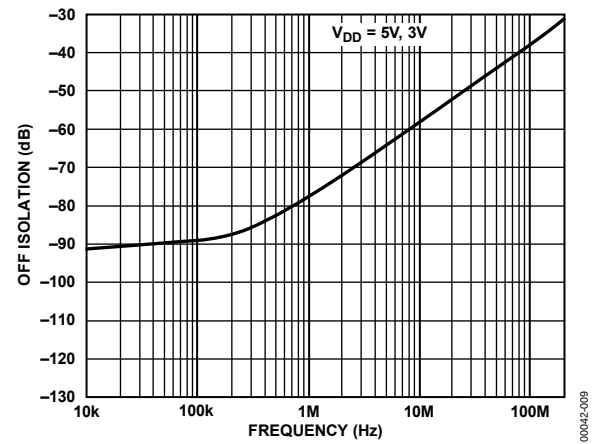


Figure 7. Off Isolation vs. Frequency

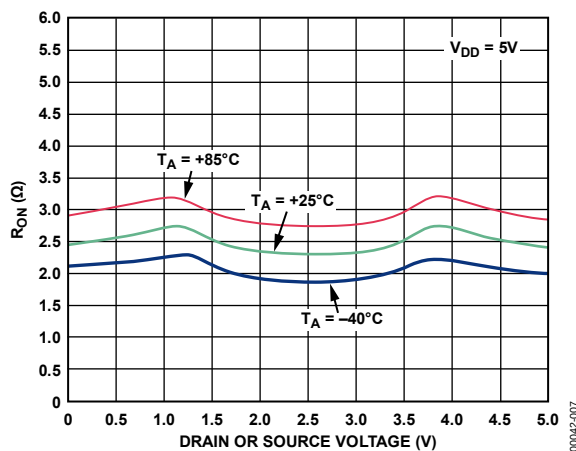


Figure 5. On Resistance as a Function of V_D (V_S) for Different Temperatures
 $V_{DD} = 5V$

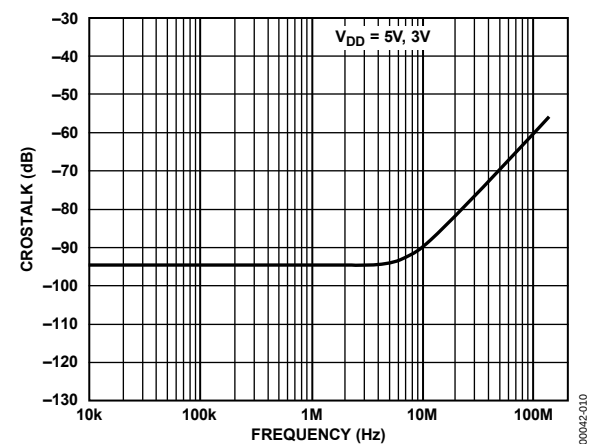


Figure 8. Crosstalk vs. Frequency

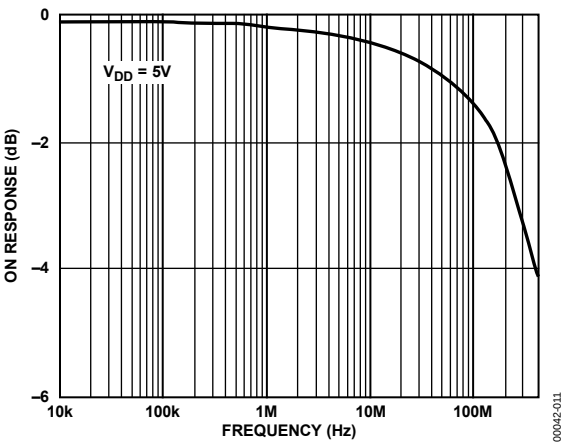


Figure 9. On Response vs. Frequency

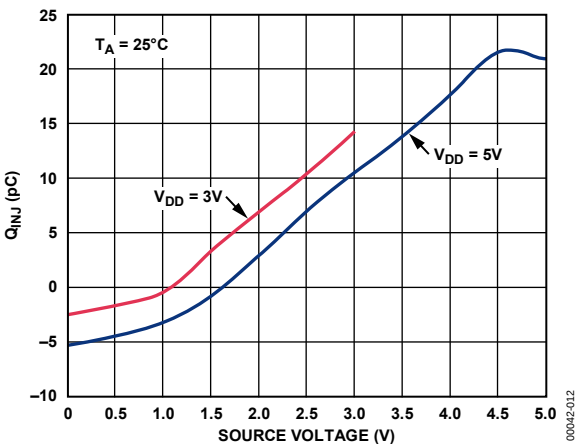
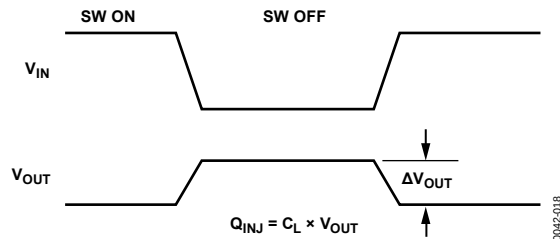
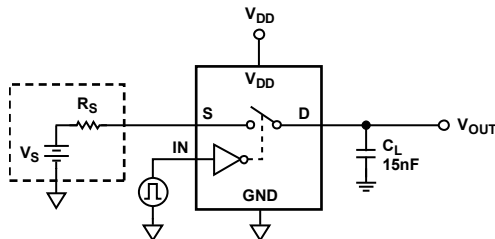
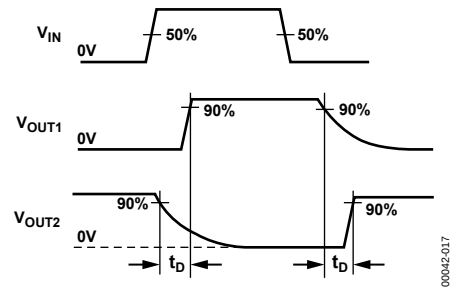
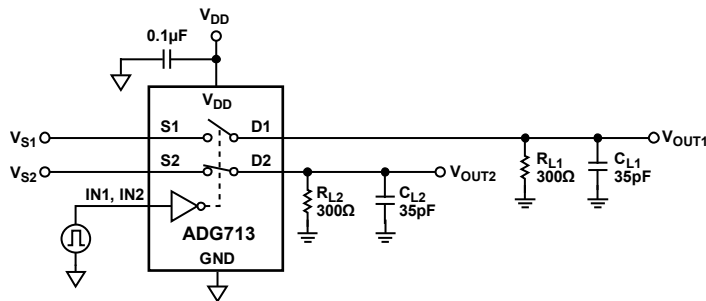
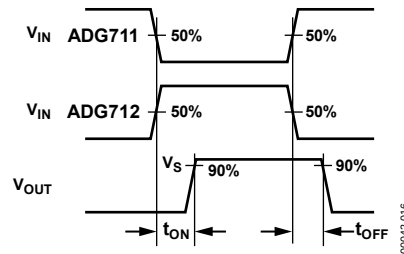
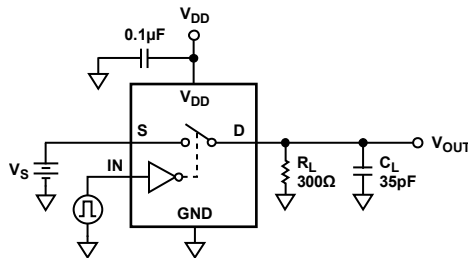
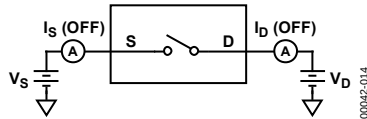
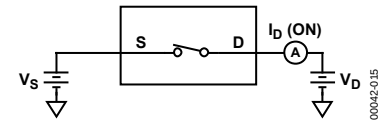
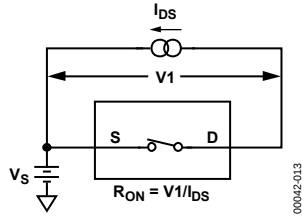


Figure 10. Charge Injection vs. Source Voltage

TEST CIRCUITS



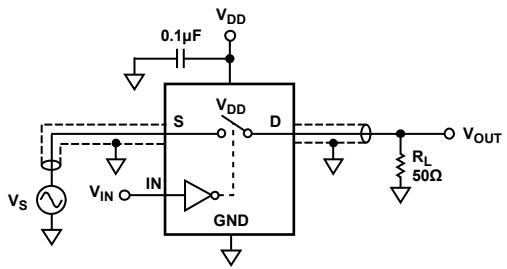


Figure 17. Off Isolation

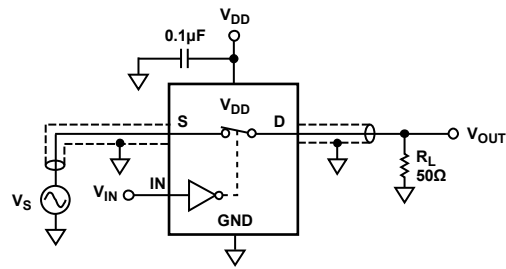
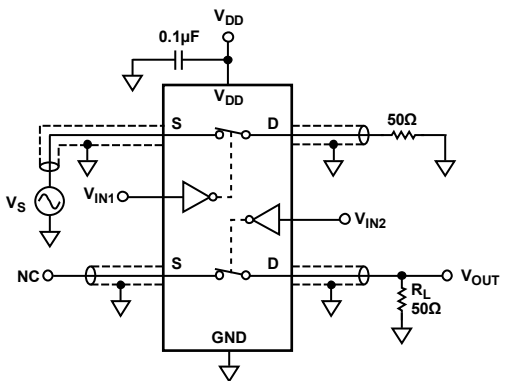


Figure 19. Bandwidth



CHANNEL-TO-CHANNEL CROSSTALK = $20 \times \log |V_S/V_{OUT}|$

Figure 18. Channel-to-Channel Crosstalk

TERMINOLOGY

R_{ON}

Ohmic resistance between D and S.

ΔR_{ON}

On resistance match between any two channels, ie., $R_{ONmax} - R_{ONmin}$.

R_{FLAT(ON)}

Flatness is defined as the difference between the maximum and minimum value of on resistance as measured over the specified analog signal range.

I_s (OFF)

Source leakage current with the switch off.

I_D (OFF)

Drain leakage current with the switch off.

I_D, I_s (ON)

Channel leakage current with the switch on.

V_D (V_s)

Analog voltage on Terminals D, S.

C_s (OFF)

Off switch source capacitance.

C_D (OFF)

Off switch drain capacitance.

C_D, C_s (ON)

On switch capacitance.

t_{ON}

Delay between applying the digital control input and the output switching on.

t_{OFF}

Delay between applying the digital control input and the output switching off.

t_D

Off time or on time measured between the 90% points of both switches, when switching from one address state to another ([ADG713](#) only).

Crosstalk

A measure of unwanted signal that is coupled through from one channel to another as a result of parasitic capacitance.

Off Isolation

A measure of unwanted signal coupling through an off switch.

Charge Injection

A measure of the glitch impulse transferred from the digital input to the analog output during switching.

Bandwidth

The frequency at which the output is attenuated by 3 dB.

On Response

The frequency response of the on switch.

APPLICATIONS INFORMATION

Figure 20 illustrates a photodetector circuit with programmable gain. An AD820 is used as the output operational amplifier.

With the resistor values shown in the circuit, and using different combinations of the switches, gain in the range of 2 to 16 can be achieved.

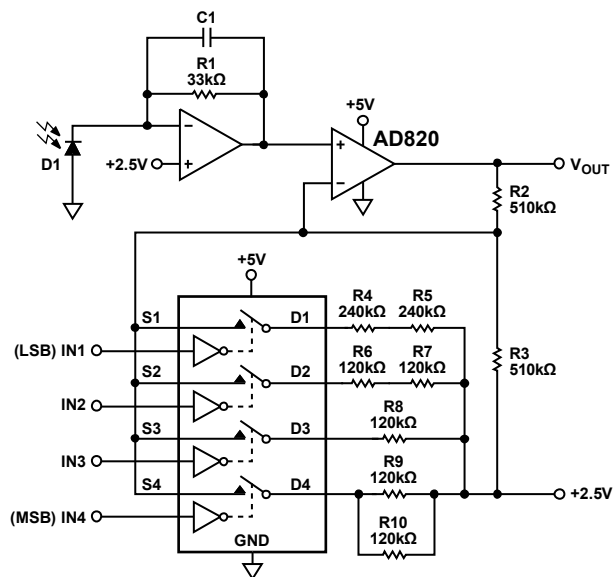
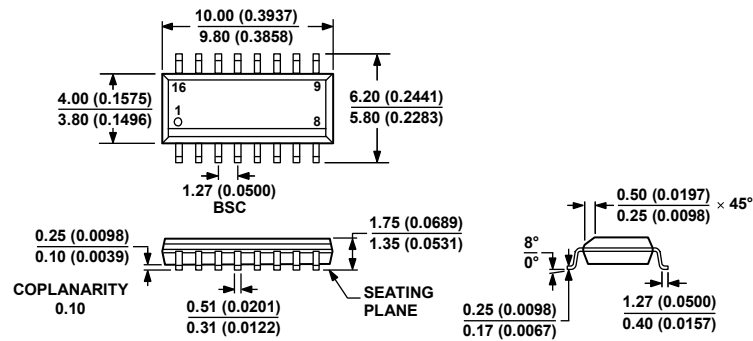


Figure 20. Photodetector Circuit with Programmable Gain

00042-022

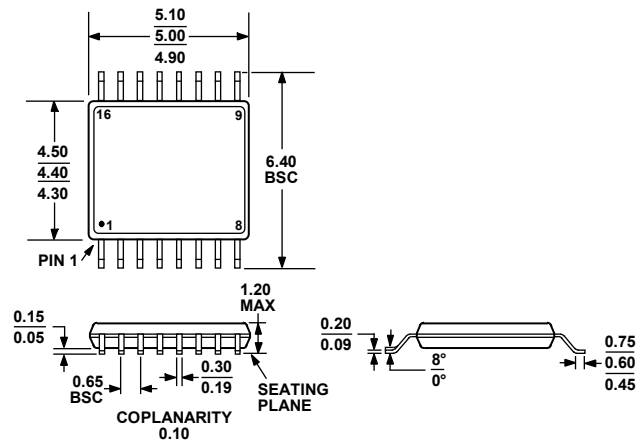
OUTLINE DIMENSIONS



COMPLIANT TO JEDEC STANDARDS MS-012-AC
CONTROLLING DIMENSIONS ARE IN MILLIMETERS; INCH DIMENSIONS
(IN PARENTHESES) ARE ROUNDED-OFF MILLIMETER EQUIVALENTS FOR
REFERENCE ONLY AND ARE NOT APPROPRIATE FOR USE IN DESIGN.

Figure 21. 16-Lead Standard Small Outline Package [SOIC]
Narrow Body
(R-16)

Dimensions shown in millimeters and (inches)



COMPLIANT TO JEDEC STANDARDS MO-153-AB

Figure 22. 16-Lead Thin Shrink Small Outline Package [TSSOP]
(RU-16)

Dimensions shown in millimeters

ADG711/ADG712/ADG713

ORDERING GUIDE

Model ^{1, 2}	Temperature range	Package Description	Package Option
ADG711BR	−40°C to +85°C	Standard Small Outline(SOIC)	R-16
ADG711BR-REEL	−40°C to +85°C	Standard Small Outline(SOIC)	R-16
ADG711BR-REEL7	−40°C to +85°C	Standard Small Outline(SOIC)	R-16
ADG711BRZ	−40°C to +85°C	Standard Small Outline(SOIC)	R-16
ADG711BRZ-REEL	−40°C to +85°C	Standard Small Outline(SOIC)	R-16
ADG711BRZ-REEL7	−40°C to +85°C	Standard Small Outline(SOIC)	R-16
ADG711BRU	−40°C to +85°C	Thin Shrink Small Outline(TSSOP)	RU-16
ADG711BRU-REEL	−40°C to +85°C	Thin Shrink Small Outline(TSSOP)	RU-16
ADG711BRU-REEL7	−40°C to +85°C	Thin Shrink Small Outline(TSSOP)	RU-16
ADG711BRUZ	−40°C to +85°C	Thin Shrink Small Outline(TSSOP)	RU-16
ADG711BRUZ-REEL	−40°C to +85°C	Thin Shrink Small Outline(TSSOP)	RU-16
ADG711BRUZ-REEL7	−40°C to +85°C	Thin Shrink Small Outline(TSSOP)	RU-16
ADG711WBRUZ-REEL	−40°C to +85°C	Thin Shrink Small Outline(TSSOP)	RU-16
ADG712BR	−40°C to +85°C	Standard Small Outline(SOIC)	R-16
ADG712BR-REEL	−40°C to +85°C	Standard Small Outline(SOIC)	R-16
ADG712BR-REEL7	−40°C to +85°C	Standard Small Outline(SOIC)	R-16
ADG712BRZ	−40°C to +85°C	Standard Small Outline(SOIC)	R-16
ADG712BRZ-REEL	−40°C to +85°C	Standard Small Outline(SOIC)	R-16
ADG712BRZ-REEL7	−40°C to +85°C	Standard Small Outline(SOIC)	R-16
ADG712BRU	−40°C to +85°C	Thin Shrink Small Outline(TSSOP)	RU-16
ADG712BRU-REEL	−40°C to +85°C	Thin Shrink Small Outline(TSSOP)	RU-16
ADG712BRU-REEL7	−40°C to +85°C	Thin Shrink Small Outline(TSSOP)	RU-16
ADG712BRUZ	−40°C to +85°C	Thin Shrink Small Outline(TSSOP)	RU-16
ADG712BRUZ-REEL	−40°C to +85°C	Thin Shrink Small Outline(TSSOP)	RU-16
ADG712BRUZ-REEL7	−40°C to +85°C	Thin Shrink Small Outline(TSSOP)	RU-16
ADG713BR	−40°C to +85°C	Standard Small Outline(SOIC)	R-16
ADG713BRZ	−40°C to +85°C	Standard Small Outline(SOIC)	R-16
ADG713BRZ-REEL	−40°C to +85°C	Standard Small Outline(SOIC)	R-16
ADG713BRZ-REEL7	−40°C to +85°C	Standard Small Outline(SOIC)	R-16
ADG713BRU	−40°C to +85°C	Thin Shrink Small Outline(TSSOP)	RU-16
ADG713BRU-REEL	−40°C to +85°C	Thin Shrink Small Outline(TSSOP)	RU-16
ADG713BRU-REEL7	−40°C to +85°C	Thin Shrink Small Outline(TSSOP)	RU-16
ADG713BRUZ	−40°C to +85°C	Thin Shrink Small Outline(TSSOP)	RU-16
ADG713BRUZ-REEL	−40°C to +85°C	Thin Shrink Small Outline(TSSOP)	RU-16
ADG713BRUZ-REEL7	−40°C to +85°C	Thin Shrink Small Outline(TSSOP)	RU-16

¹ Z = RoHS Compliant Part.

² W = Qualified for Automotive Applications.

AUTOMOTIVE PRODUCTS

The AD711W models are available with controlled manufacturing to support the quality and reliability requirements of automotive applications. Note that these automotive models may have specifications that differ from the commercial models; therefore, designers should review the Specifications section of this data sheet carefully. Only the automotive grade products shown are available for use in automotive applications. Contact your local Analog Devices account representative for specific product ordering information and to obtain the specific Automotive Reliability reports for these models.

NOTES

NOTES



**Стандарт
Электрон
Связь**

Мы молодая и активно развивающаяся компания в области поставок электронных компонентов. Мы поставляем электронные компоненты отечественного и импортного производства напрямую от производителей и с крупнейших складов мира.

Благодаря сотрудничеству с мировыми поставщиками мы осуществляем комплексные и плановые поставки широчайшего спектра электронных компонентов.

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Минимальные сроки поставки, гибкие цены, неограниченный ассортимент и индивидуальный подход к клиентам являются основой для выстраивания долгосрочного и эффективного сотрудничества с предприятиями радиоэлектронной промышленности, предприятиями ВПК и научно-исследовательскими институтами России.

С нами вы становитесь еще успешнее!

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